

### KSC3296

## **Power Amplifier Applications**

• Complement to KSA1304



## **NPN Epitaxial Silicon Transistor**

### Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CBO</sub>	Collector-Base Voltage	150	V	
$V_{CEO}$	Collector-Emitter Voltage	150	V	
$V_{EBO}$	Emitter-Base Voltage	5	V	
I <sub>C</sub>	Collector Current(DC)	1.5	Α	
I <sub>B</sub>	Base Current	0.5	Α	
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	20	W	
TJ	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C	

### Electrical Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 120V, I_{E} = 0$			10	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			10	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 10V, I_{C} = 500mA$	40	75	140	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$			1.5	V
V <sub>BE</sub> (on)	Base-Emitter ON Voltage	$V_{CE} = 10V, I_{C} = 500mA$	0.65	0.75	0.85	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 500mA$		4		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10V, f = 1MHz		35		pF

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# **Typical Characteristics**

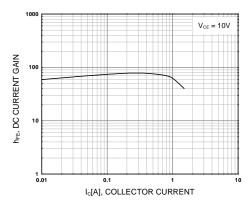


Figure 1. DC current Gain

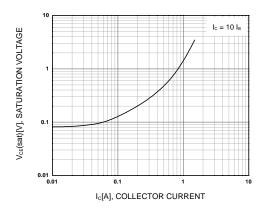


Figure 2. Collector-Emitter Saturation Voltage

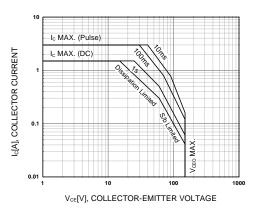


Figure 3. Safe Operating Area

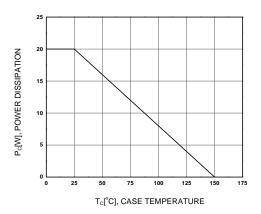
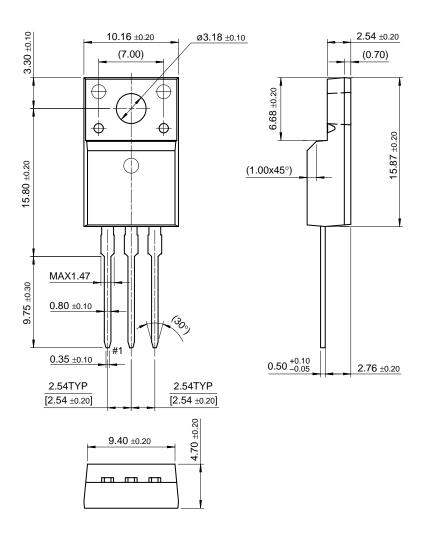


Figure 4. Power Derating

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## **Package Demensions**

## TO-220F



Dimensions in Millimeters

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